

Silicon NPN Darlington Power Transistor

DESCRIPTION :

- High DC Current Gain-
 $h_{FE} = 1000(\text{Min.}) @ I_C=25A$
 $h_{FE} = 400(\text{Min.}) @ I_C=50A$
- Collector-Emitter Breakdown Voltage
 $V_{(BR)CEO} = 120V(\text{Min})$
- Complement to the PNP MJ11033
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS :

- Designed for use as output devices in complementary general purpose amplifier applications.

NPN

MJ11032

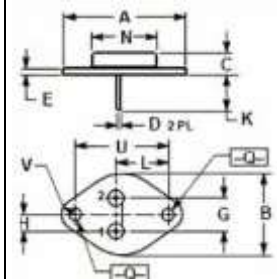
**50 AMPERES
POWER
DARLINGTON
TRANSISTOR
120 VOLTS
300 WATTS**



TO-3

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current-Continuous	I_C	50	A
Collector Current-Peak	I_{CM}	100	A
Base Current-Continuous	I_B	2	A
Collector Power Dissipation @ $T_c=25^\circ\text{C}$	P_C	300	Watts
Max. Junction Temperature	T_J	200	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +200	$^\circ\text{C}$



PIN 1.BASE.
2.EMITTER
COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	39.00	
B	25.2	26.67
C	8.30	8.90
D	1.45	1.60
E	1.50	1.70
G	11.00	
H	5.50	
K	10.50	13.50
L	16.75	17.05
N	19.40	19.62
O	4.00	4.20
U	29.00	31.00
V	4.00	4.20

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R_{thj-c}	0.584	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 50\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	120		V
Collector Cutoff Current ($V_{CB} = 120\text{ V}$, $I_E = 0$)	I_{CBO}		2.0	mA
Collector Cutoff Current ($V_{CE} = 120\text{ V}$, $I_B = 0$)	I_{CEO}		2.0	mA
Emitter Cutoff Current ($V_{EB} = 5\text{ V}$, $I_C = 0$)	I_{EBO}		5.0	mA

ON CHARACTERISTICS(1)

DC Current Gain ($I_C = 25\text{ A}$, $V_{CE} = 5\text{ V}$) ($I_C = 50\text{ A}$, $V_{CE} = 5\text{ V}$)	h_{FE}	1000 400	18000	
Collector-Emitter Saturation Voltage ($I_C = 25\text{ A}$, $I_B = 250\text{ mA}$) ($I_C = 50\text{ A}$, $I_B = 500\text{ mA}$)	$V_{CE(SAT)}$		2.5 3.5	V
Base-Emitter Saturation Voltage ($I_C = 25\text{ A}$, $I_B = 250\text{ mA}$) ($I_C = 50\text{ A}$, $I_B = 500\text{ mA}$)	$V_{BE(SAT)}$		3.0 4.5	V

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